

Preliminary Amendment

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For: DIFFUSION BARRIER LAYERS AND METHODS OF FORMING SAME

44. (New) The structure of claim 23, wherein the substrate assembly comprises at least one active device.
45. (New) The structure of claim 37, wherein the barrier layer comprises a chemical vapor deposited barrier layer.
46. (New) The structure of claim 37, wherein the substrate assembly comprises a small high aspect ratio opening, and further wherein the interconnect is formed in the small high aspect ratio opening relative to the at least one active device.
47. (New) The structure of claim 37, wherein a thickness of the barrier layer is in a range of about 10 Å to about 10,000 Å.
48. (New) The structure of claim 47, wherein the thickness of the barrier layer is in a range of about 100 Å to about 500 Å.
49. (New) The structure of claim 39, wherein x is about 0.95.
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